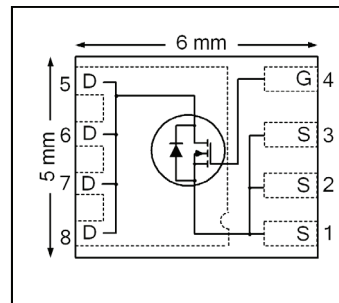


HEXFET® Power MOSFET

V_{DSS}	40	V
R_{DS(on)} max (@ V _{GS} = 10V)	3.3	mΩ
Q_g (typical)	39	nC
I_D (@T _{C (Bottom)} = 25°C)	50	A


Applications

- Secondary Side Synchronous Rectification
- Inverters for DC Motors
- DC-DC Brick Applications
- Boost Converters

Features

Low R _{DS(ON)} (< 4.7mΩ @ V _{GS} = 4.5V)
Low Thermal Resistance to PCB (<1.2°C/W)
Low Profile (<0.9mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Industrial Qualification

results in
⇒

Benefits

Lower Conduction Losses
Enables better thermal dissipation
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Orderable Part Number	Package Type	Standard Pack		Note
		Form	Quantity	
IRLH7134TRPbF	PQFN 5mm x 6 mm	Tape and Reel	4000	
IRLH7134TR2PbF	PQFN 5mm x 6 mm	Tape and Reel	400	EOL notice # 259

Absolute Maximum Ratings

	Parameter	Max.	Units
V _{DS}	Drain-to-Source Voltage	40	V
V _{GS}	Gate-to-Source Voltage	± 16	
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	26	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	21	
I _D @ T _{C(Bottom)} = 25°C	Continuous Drain Current, V _{GS} @ 10V	134⑥⑦	
I _D @ T _{C(Bottom)} = 100°C	Continuous Drain Current, V _{GS} @ 10V	85⑥⑦	
I _D @ T _{C(Bottom)} = 25°C	Continuous Drain Current, V _{GS} @ 10V (Package Limited)	50⑦	
I _{DM}	Pulsed Drain Current ①	640	
P _D @ T _A = 25°C	Power Dissipation ⑤	3.6	W
P _D @ T _{C(Bottom)} = 25°C	Power Dissipation ⑤	104	
	Linear Derating Factor ⑤	0.029	W/°C
T _J	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range		

Notes ① through ⑦ are on page 9

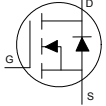
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	37	—	mV/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	2.8	3.3	m Ω	$V_{GS} = 10V, I_D = 50A$ ③
		—	3.9	4.9		$V_{GS} = 4.5V, I_D = 40A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 100\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-5.6	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 40V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
g_{fs}	Forward Transconductance	120	—	—	S	$V_{DS} = 10V, I_D = 50A$
Q_g	Total Gate Charge	—	39	58	nC	$V_{DS} = 20V$ $V_{GS} = 4.5V$ $I_D = 50A$
Q_{gs1}	Pre-V _{th} Gate-to-Source Charge	—	9.0	—		
Q_{gs2}	Post-V _{th} Gate-to-Source Charge	—	4.5	—		
Q_{gd}	Gate-to-Drain Charge	—	16	—		
Q_{godr}	Gate Charge Overdrive	—	9.5	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	20.5	—		
Q_{oss}	Output Charge	—	23	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
R_G	Gate Resistance	—	0.6	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	21	—	ns	$V_{DD} = 20V, V_{GS} = 4.5V$ $I_D = 50A$ $R_G = 1.7\Omega$
t_r	Rise Time	—	75	—		
$t_{d(off)}$	Turn-Off Delay Time	—	18	—		
t_f	Fall Time	—	13	—		
C_{iss}	Input Capacitance	—	3720	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	610	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	350	—		$f = 1.0\text{MHz}$

Avalanche Characteristics

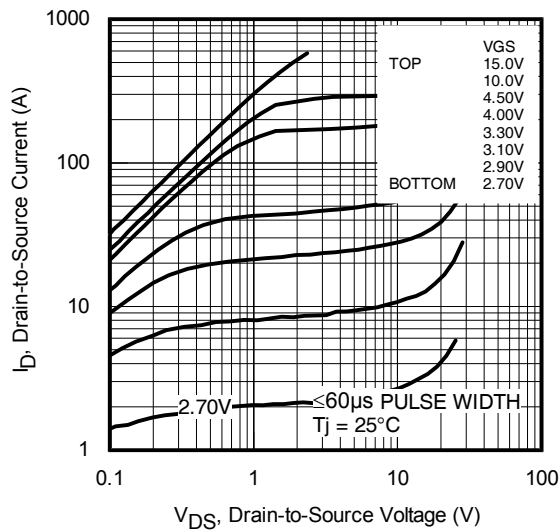
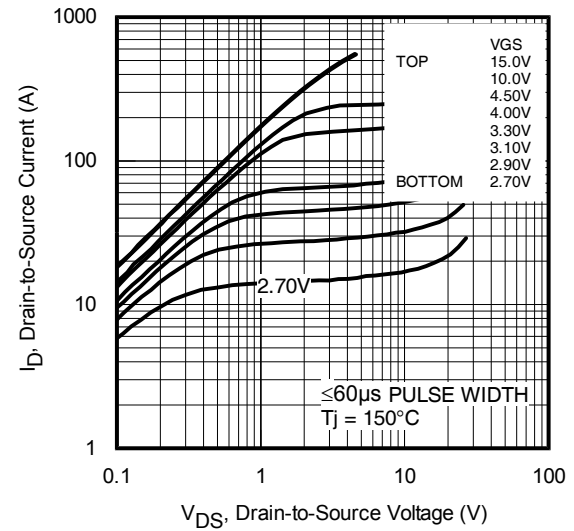
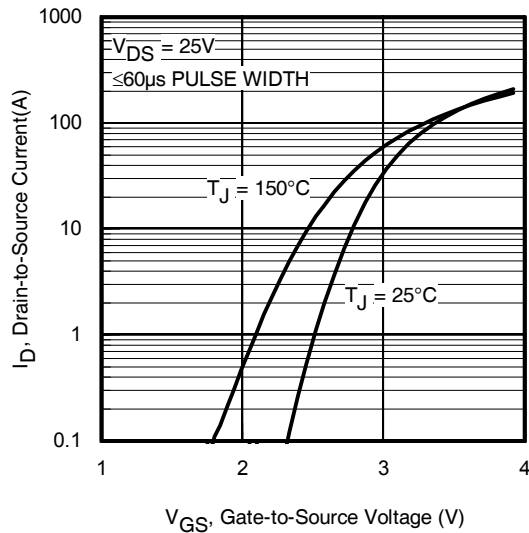
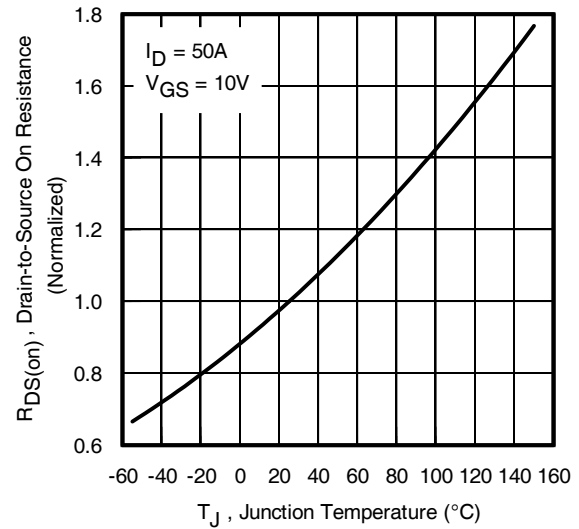
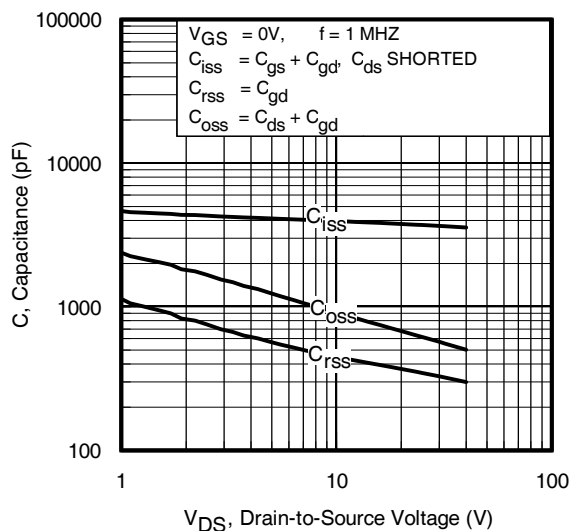
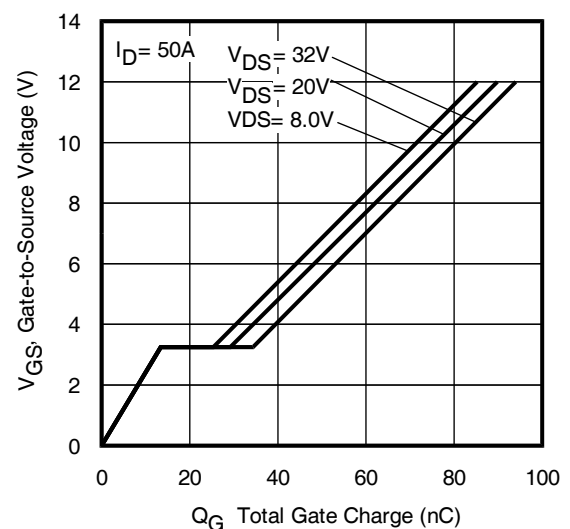
	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	125	mJ
I_{AR}	Avalanche Current ①	—	50	A

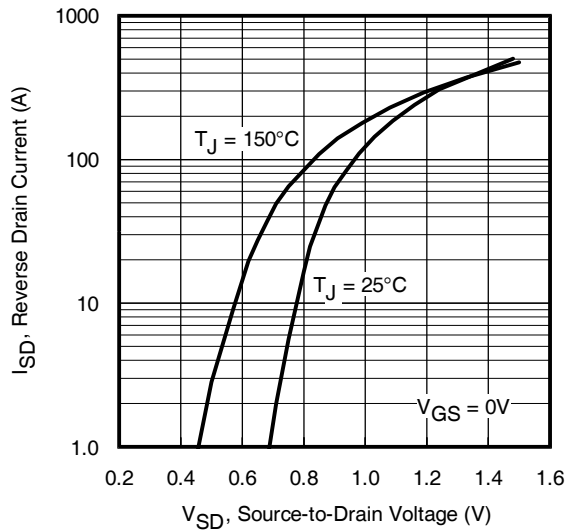
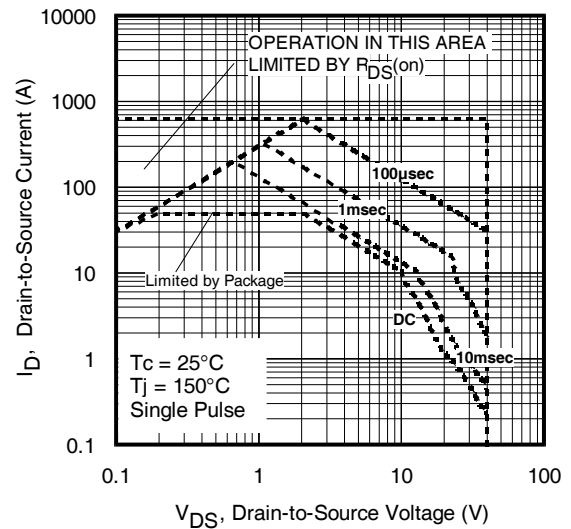
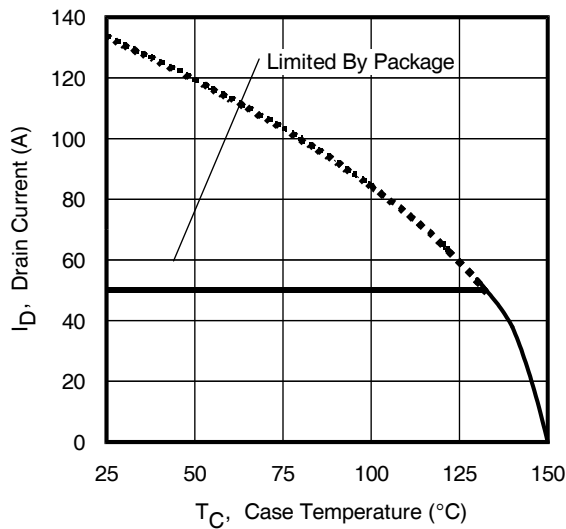
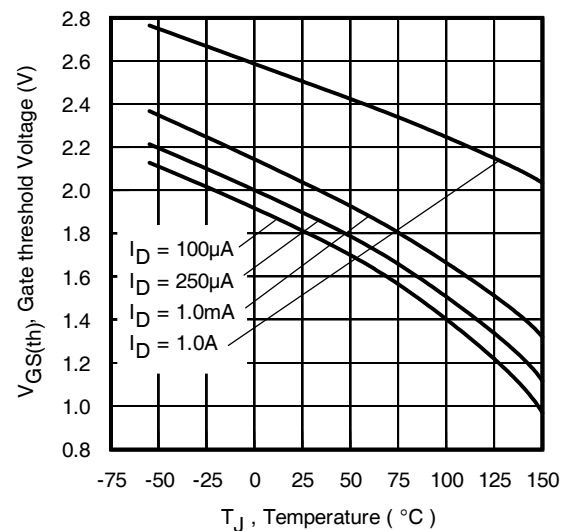
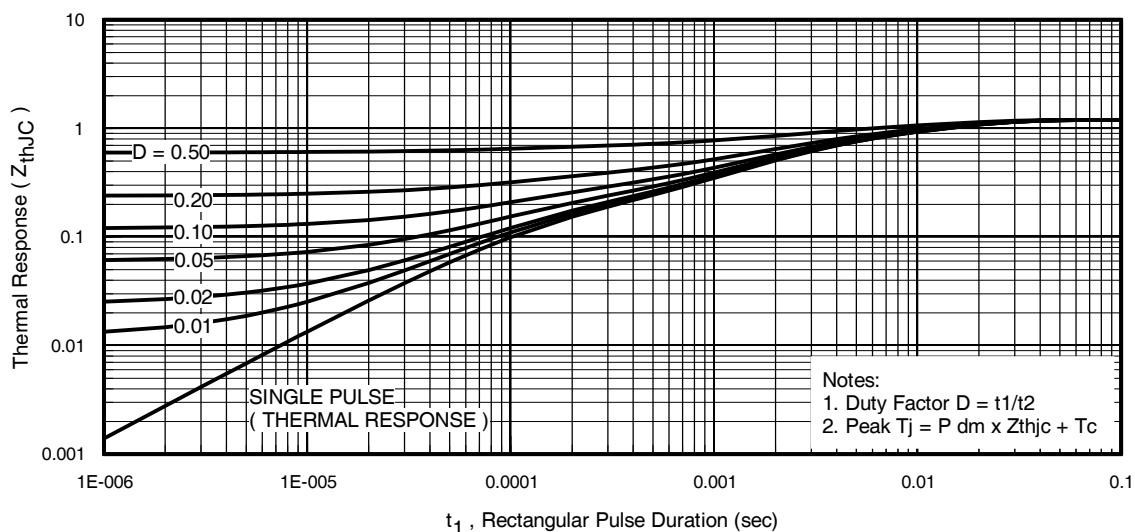
Diode Characteristics

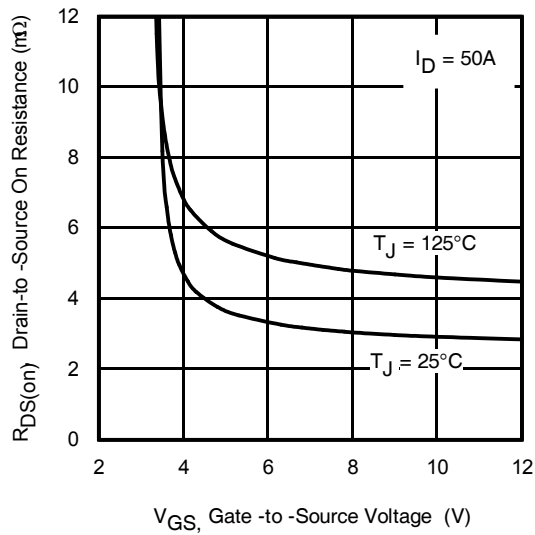
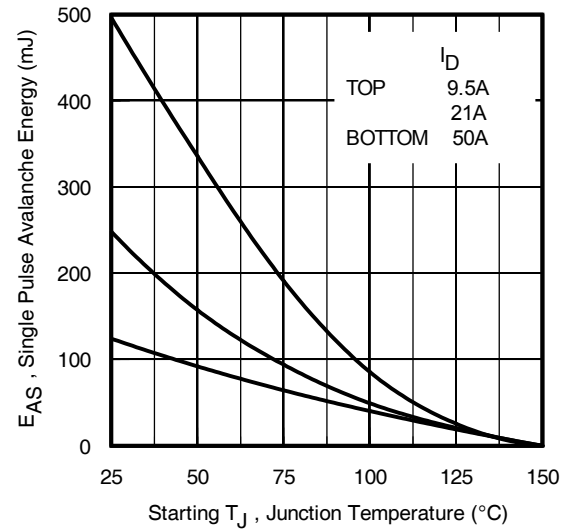
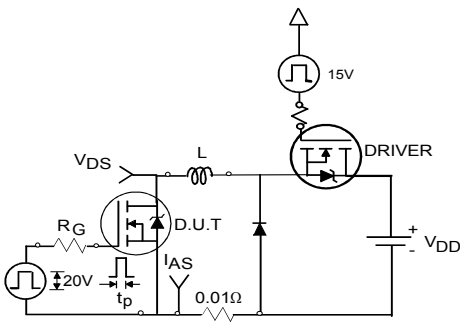
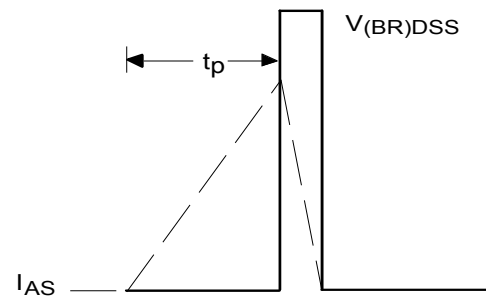
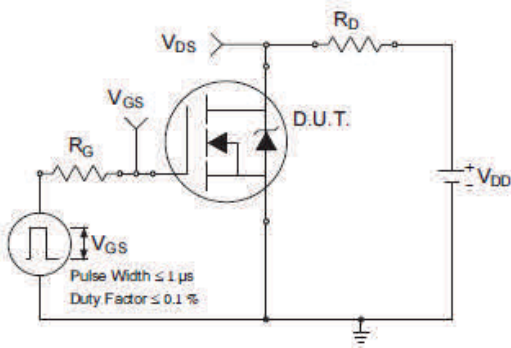
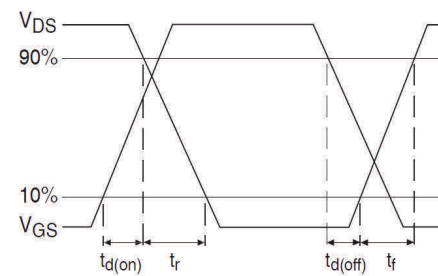
	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	50⑦	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	640		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 50A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	25	38	ns	$T_J = 25^\circ\text{C}, I_F = 50A, V_{DD} = 20V$
Q_{rr}	Reverse Recovery Charge	—	74	110	nC	$di/dt = 400A/\mu s$ ③
t_{on}	Forward Turn-On Time	Time is dominated by parasitic Inductance				

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (Bottom)	Junction-to-Case ④	—	1.2	$^\circ\text{C/W}$
$R_{\theta JC}$ (Top)	Junction-to-Case ④	—	30	
$R_{\theta JA}$	Junction-to-Ambient ⑤	—	35	
$R_{\theta JA} (<10s)$	Junction-to-Ambient ⑤	—	22	


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10. Threshold Voltage vs. Temperature

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig 12. On-Resistance vs. Gate Voltage

Fig 13. Maximum Avalanche Energy vs. Drain Current

Fig 14a. Unclamped Inductive Test Circuit

Fig 14b. Unclamped Inductive Waveforms

Fig 15a. Switching Time Test Circuit

Fig 15b. Switching Time Waveforms

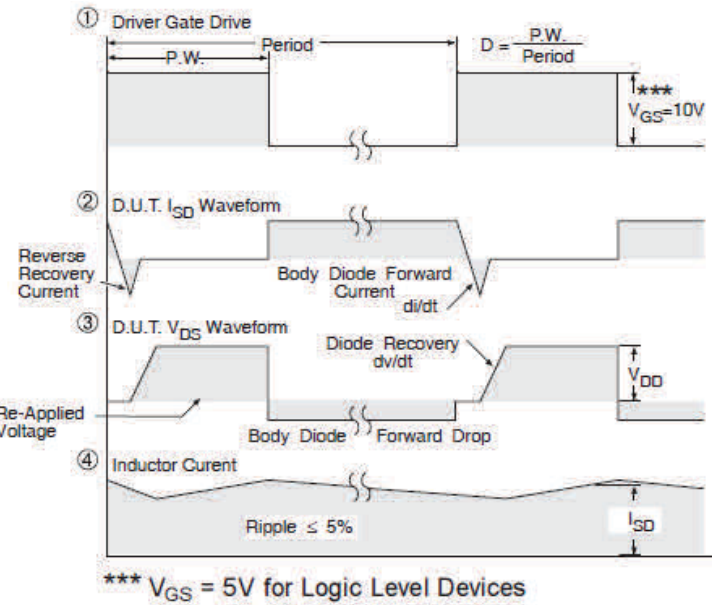
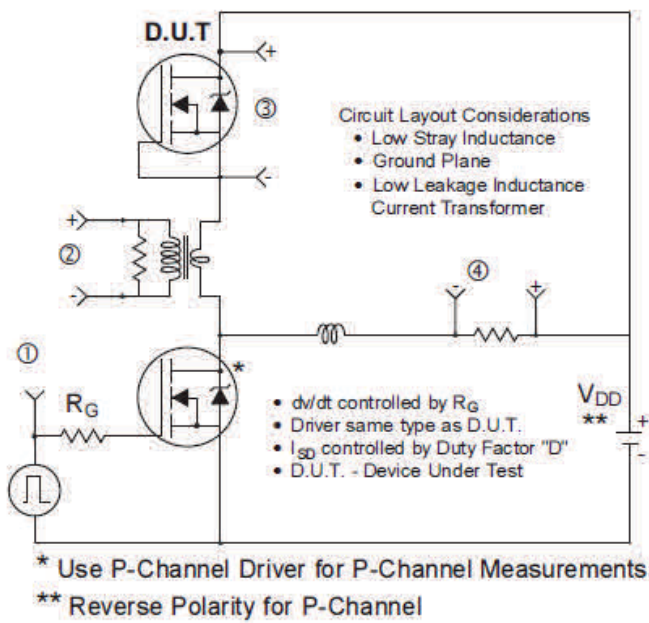


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

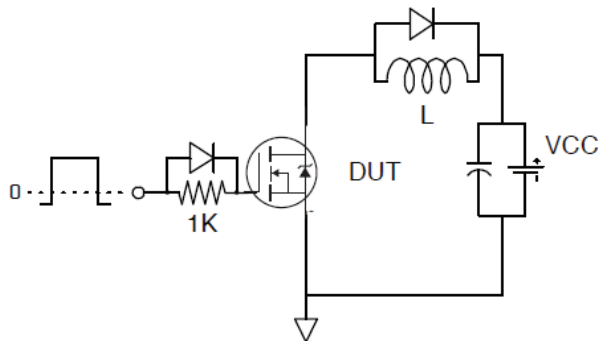


Fig 17. Gate Charge Test Circuit

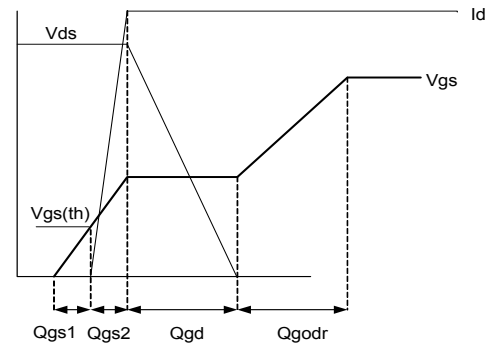
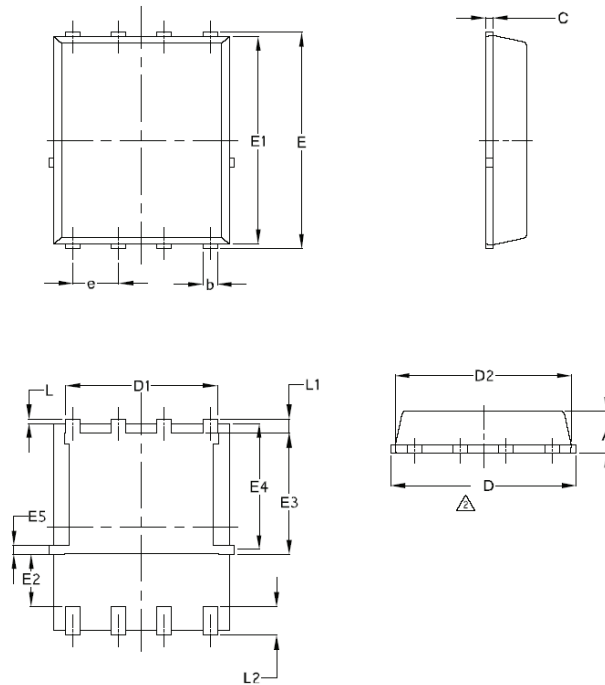


Fig 18. Gate Charge Waveform

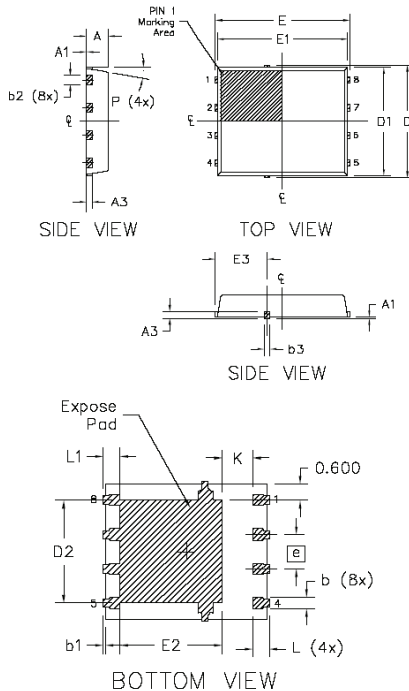
VDD

PQFN 5x6 Outline "E" Package Details



SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.90	1.17	0.0354	0.0461
b	0.33	0.48	0.0130	0.0189
C	0.195	0.300	0.0077	0.0118
D	4.80	5.15	0.1890	0.2028
D1	3.91	4.31	0.1539	0.1697
D2	4.80	5.00	0.1890	0.1968
E	5.90	6.15	0.2323	0.2421
E1	5.65	6.00	0.2224	0.2362
E2	1.51	—	0.0594	—
E3	3.32	3.78	0.1307	0.1480
E4	3.42	3.58	0.1346	0.1409
E5	0.18	0.32	0.0071	0.0126
e	1.27	BSC	0.050	BSC
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.66	0.0150	0.0260
L2	0.51	0.86	0.0201	0.0339
I	0	0.18	0	0.0071

PQFN 5x6 Outline "G" Package Details



DIM SYMBOL	MILLIMETERS		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.950	1.050	0.0374	0.0413
A1	0.000	0.050	0.0000	0.0020
A3	0.254	REF	0.0100	REF
b	0.310	0.510	0.0122	0.0201
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.180	0.450	0.0071	0.0177
D	5.150	BSC	0.2028	BSC
D1	5.000	BSC	0.1969	BSC
D2	3.700	3.900	0.1457	0.1535
E	6.150	BSC	0.2421	BSC
E1	6.000	BSC	0.2362	BSC
E2	3.560	3.760	0.1402	0.1488
E3	2.270	2.470	0.0894	0.0972
e	1.27	REF	0.050	REF
K	0.830	1.400	0.0327	0.0551
L	0.510	0.710	0.0201	0.0280
L1	0.510	0.710	0.0201	0.0280
P	10 deg	12 deg	0 deg	12 deg

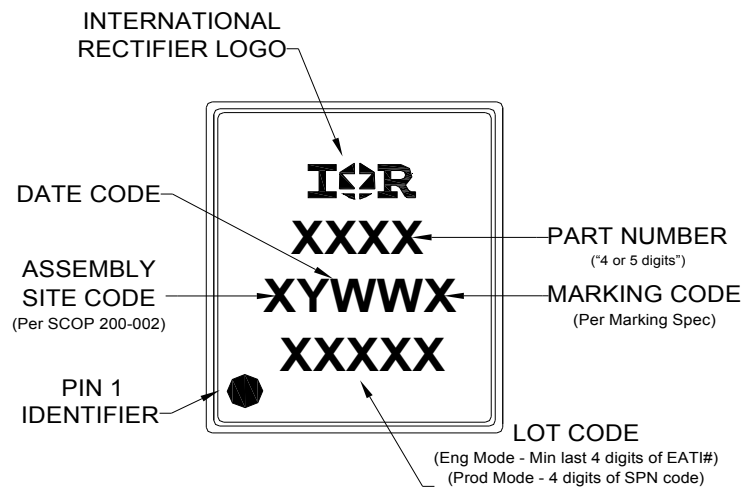
Note:

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

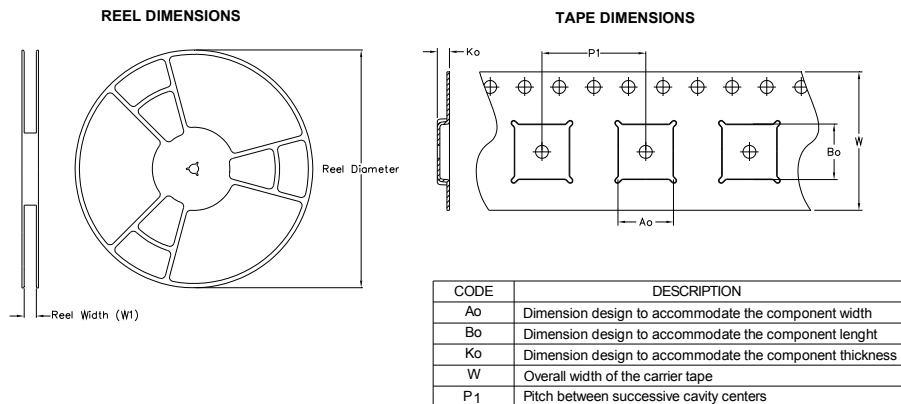
For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: <http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154: <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

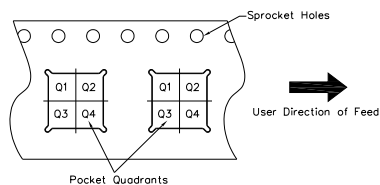
PQFN 5x6 Part Marking



PQFN 5x6 Tape and Reel



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Note: All dimension are nominal

Package Type	Reel Diameter (Inch)	QTY	Reel Width W1 (mm)	Ao (mm)	Bo (mm)	Ko (mm)	P1 (mm)	W (mm)	Pin 1 Quadrant
5 X 6 PQFN	13	4000	12.4	6.300	5.300	1.20	8.00	12	Q1

Qualification Information[†]

Qualification Level	Industrial (per JEDEC JESD47F [†] guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D [†])
RoHS Compliant	Yes	

[†] Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^{\circ}\text{C}$, $L = 0.099\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 50\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_{θ} is measured at T_J of approximately 90°C .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.
- ⑥ Calculated continuous current based on maximum allowable junction temperature.
- ⑦ Package is limited to 50A by die-source to lead-frame bonding technology.

Revision History

Date	Comment
5/13/2014	- Updated ordering information to reflect the End-Of-life (EOL) of the mini-reel option (EOL notice #259) - Updated Tape and Reel on page 8. - Updated data sheet based on corporate template.
6/2/2015	- Updated package outline for "option E" and added package outline for "option G" on page 7. - Updated "IFX" logo on page 1 & 9. - Updated tape and reel on page 8.
7/7/2015	Corrected package outline for "option E" on page 7.
8/01/2016	- Updated "Infineon" logo –all pages. - Updated disclaimer on last page. - Corrected typo on switch time test condition from "$V_{GS} = 10V$" to "$V_{GS} = 4.5V$" on page 2.

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